Powering the SiC evolution™

GP2T080A120H

V_{DS}	1200 V
$R_{DS,on}$	77 mΩ
$I_{D\ (TC=25C)}$	35 A
$T_{J,max}$	175°C

QSiC™ 1200V SiC MOSFET

Features

- High speed switching
- Reliable body diode
- All parts tested to above 1400V
- Avalanche tested to 200mJ
- Driver source pin for gate driving
- Increased creepage due to notched design

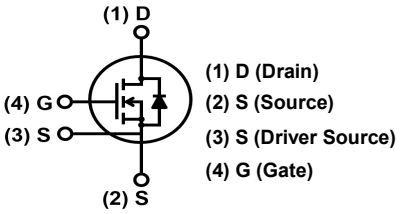
Benefits

- Lower capacitance
- Higher system efficiency
- Easy to parallel
- Lower Qg

Applications

- Solar Inverters
- Switch mode power supplies, UPS
- Induction Heating and Welding
- EV charging stations
- High Voltage DC/DC Converters
- Motor Drives

Package



Part #	Package	Marking
GP2T080A120H	TO-247-4L	2T080A120

Maximum Ratings, at T_J=25°C, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	V_{rated}	V_{GS}=0V, I_D=1μA	1200	V
Continuous Drain Current	I_D	T_C=25°C, V_{GS}=20V	35	A
		T_C=100°C, V_{GS}=20V	26	
Pulsed Drain Current	$I_{D,pulse}$	T_C=25°C	80	
Gate Source Voltage	V_{GSmax}		-10/25	V
	V_{GSop}	Recommended operational	-5/20	
Power Dissipation	P_{tot}	T_C=25°C	188	W
Operating & Storage Temperature	T_J, $T_{storage}$	Continuous	-55...175	°C
Single Pulse Avalanche Energy	E_{AS}	L=1mH, I_{AS}=20.0A, V=50V	200	mJ

Thermal Characteristics

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal Resistance, Junction to Case	R_{thJC}		-	0.65	0.80	°C/W
Thermal Resistance, Junction to Ambient	R_{thJA}		-	-	40.0	

Static Electrical Characteristics, at T_J=25°C, unless otherwise specified

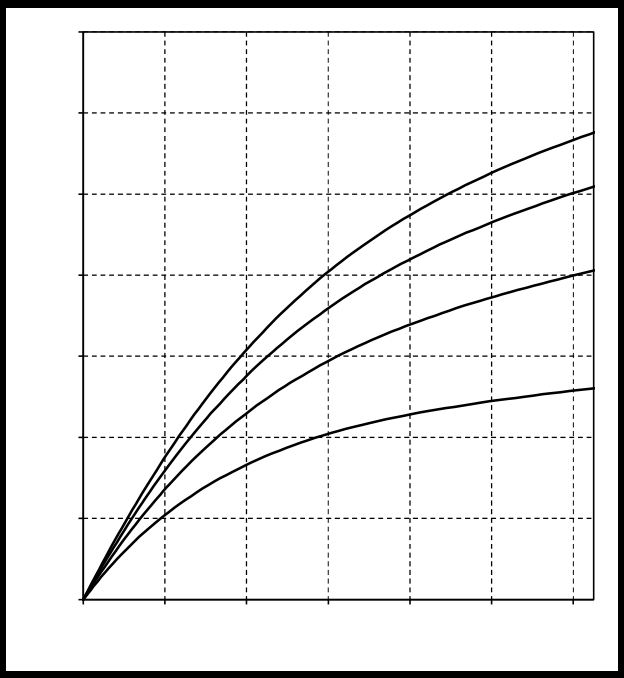
Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=1mA	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=1200V, V_{GS}=0V	-	0.1	1.0	μA
		V_{DS}=1200V, V_{GS}=0V, T_J=175°C	-	1	-	
Gate-Source Leakage Current	I_{GSS+}	V_{GS}=20V, V_{DS}=0V	-	10	100	nA
	I_{GSS-}	V_{GS}=-5V, V_{DS}=0V	-	-10	-100	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=10mA	1.8	2.8	4	V
		V_{GS}=V_{DS}, I_D=10mA, T_J=125°C	-	2.1	-	
		V_{GS}=V_{DS}, I_D=10mA, T_J=175°C	-	1.9	-	
Drain-Source On-Resistance	R_{DSon}	V_{GS}=20V, I_D=20A	-	77	100	mΩ
		V_{GS}=20V, I_D=10A	-	71	90	
		V_{GS}=20V, I_D=20A, T_J=125°C	-	106	-	
		V_{GS}=20V, I_D=20A, T_J=175°C	-	134	-	
Gate Input Resistance	R_G	f=1MHz, VAC=25mV, D-S Short	-	3.0	-	Ω

AC Electrical Characteristics, at T_J=25°C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	C_{ISS}	V_{GS}=0V V_{DS}=1000V f=200kHz. Vac=25mV	-	1377	-	pF
Output Capacitance	C_{OSS}		-	62	-	
Reverse Transfer Capacitance	C_{RSS}		-	4	-	
Coss Stored Energy	E_{OSS}		-	38	-	μJ
Turn-On Switching Energy	E_{ON}	V_{DD}=800V, I_{DS}=20A, $R_{G(ext)}$=2.5Ω, V_{GS}=-5/+20V, L=975μH, FWD = GP2T080A120H	-	208	-	
Turn-Off Switching Energy	E_{OFF}		-	25	-	
Total Switching Energy	E_{TOT}		-	233	-	
Turn-On Switching Energy	E_{ON}	V_{DD}=800V, I_{DS}=20A, $R_{G(ext)}$=2.5Ω, V_{GS}=-5/+20V, L=975μH, FWD = GP3D010A120A	-	167	-	μJ
Turn-Off Switching Energy	E_{OFF}		-	27	-	
Total Switching Energy	E_{TOT}		-	194	-	
Turn-On Delay Time	$t_{D(on)}$	V_{DD}=800V, I_{DS}=20A, $R_{G(ext)}$=2.5Ω, V_{GS}=-5V/20V, L=975μH, FWD = GP2T080A120H	-	9	-	ns
Rise Time	t_R		-	4	-	
Turn-Off Delay Time	$t_{D(off)}$		-	15	-	
Fall Time	t_F		-	10	-	
Total Gate Charge	Q_G	V_{DD}=800V, I_{DS}=20A V_{GS}=-5/20V	-	61	-	nC
Gate to Source Charge	Q_{GS}		-	24	-	
Gate to Drain Charge	Q_{GD}		-	14	-	

Body Diode Characteristics, at T_J=25°C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Max Continuous Diode Fwd Current	I_S	V_{GS}=-5V, T_C=25°C	-	-	43	A
Diode Forward Voltage	V_{SD}	V_{GS}=-5V, I_S=10A	-	3.8	-	V
Reverse Recovery Time	t_{RR}	I_S=20A, V_R=800V, V_{GS}=-5V di_F/dt=8.0A/ns	-	8	-	ns
Reverse Recovery Charge	Q_{RR}		-	130	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	29	-	A



Conditions:
T_j = 175°C
tp = 100 µs

Vgs = 20V

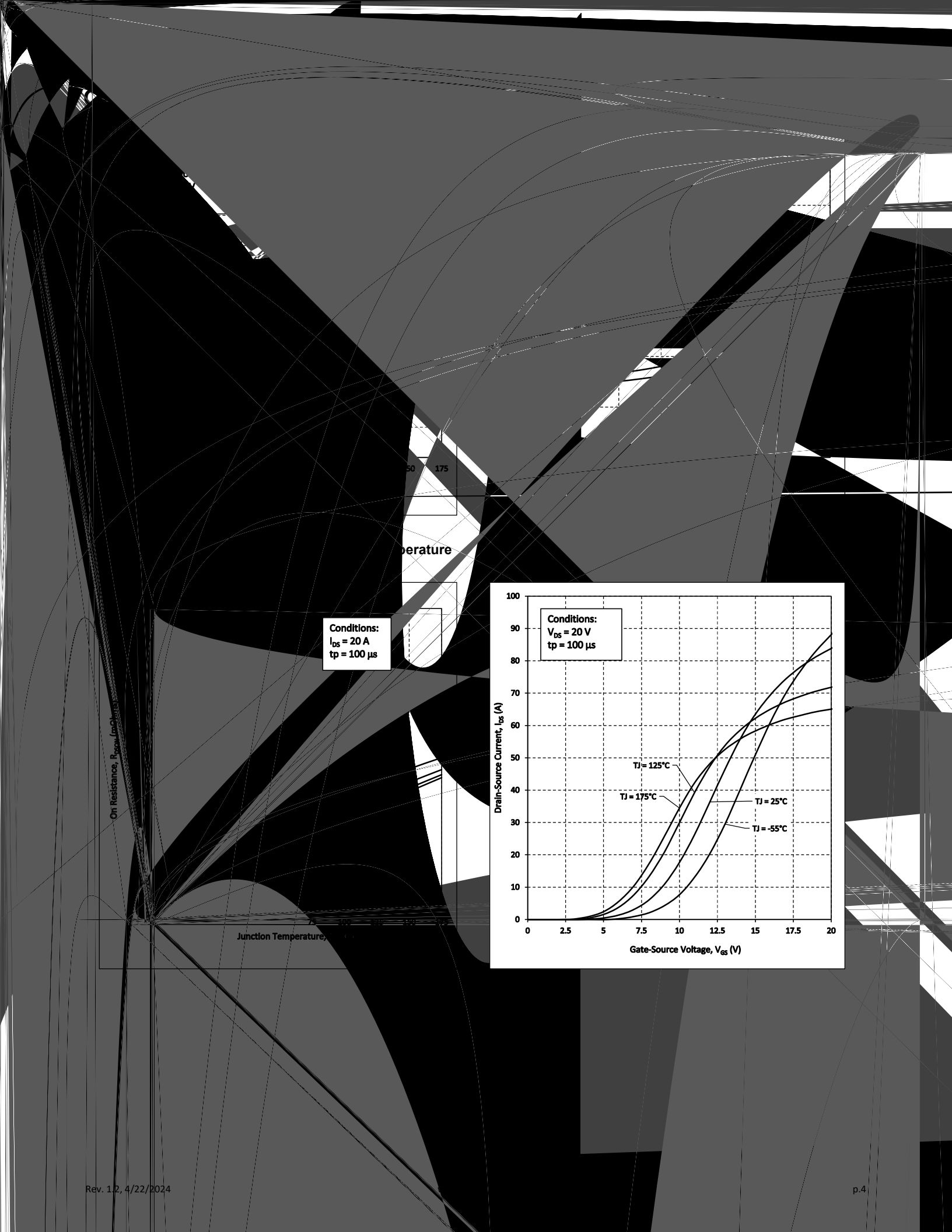
Vgs = 16V

Vgs = 14V

Vgs = 18V

Vgs = 12V

Vgs = 10V


Conditions:
I_{DS} = 20 A
tp = 100 µs
Conditions:
V_{DS} = 20 V
tp = 100 µs
TJ = 125°C
TJ = 175°C
TJ = 25°C
TJ = -55°C
Drain-Source Current, I_{DS} (A)
Gate-Source Voltage, V_{GS} (V)
0
10
20
30
40
50
60
70
80
90
100
0
2.5
5
7.5
10
12.5
15
17.5
20

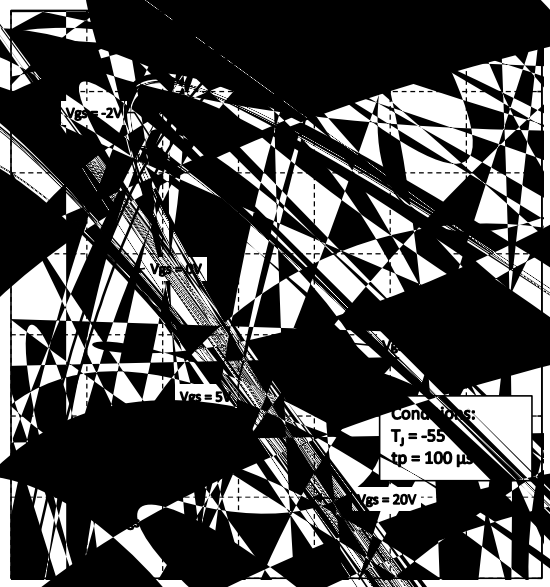
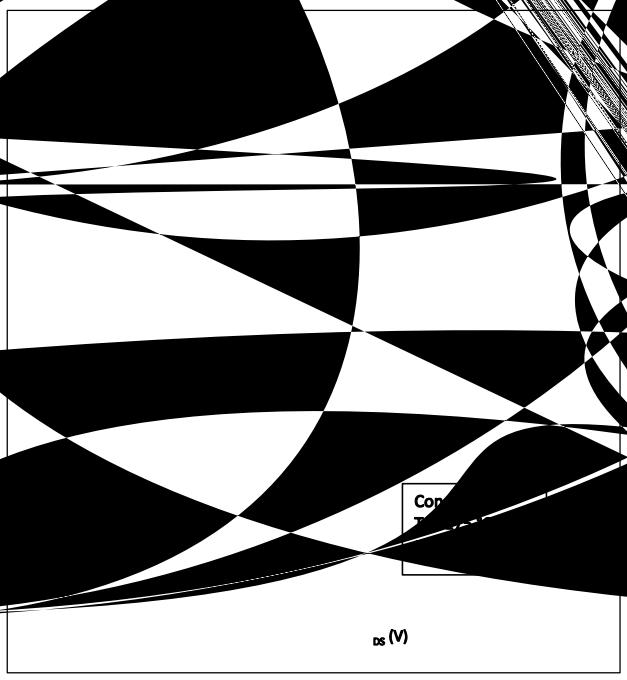


Figure 9. Bod[illegible] Characte[illegible]at TJ = -55°

Figure 10. [illegible] Diode Characte[illegible] TJ = 25°C



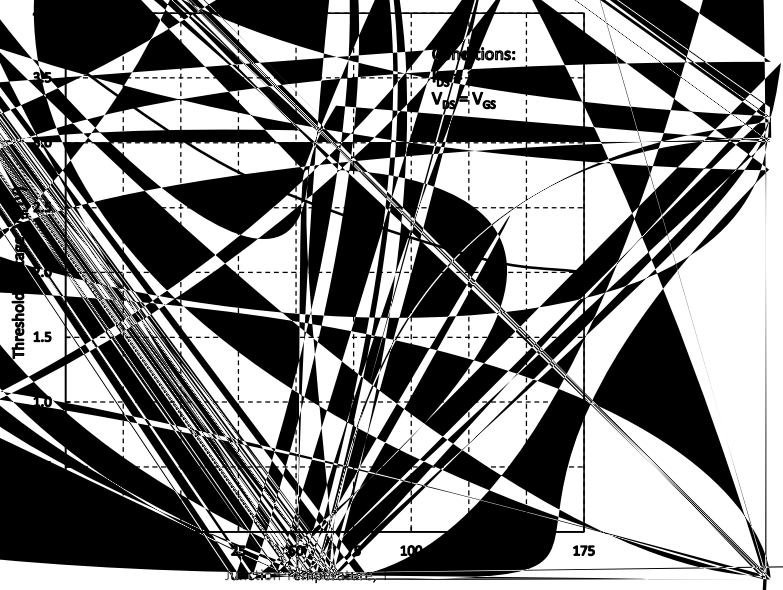


Figure 11. Body Diode Characteristics at TJ = 175°C

Figure 12. Threshold Voltage vs. Temperature

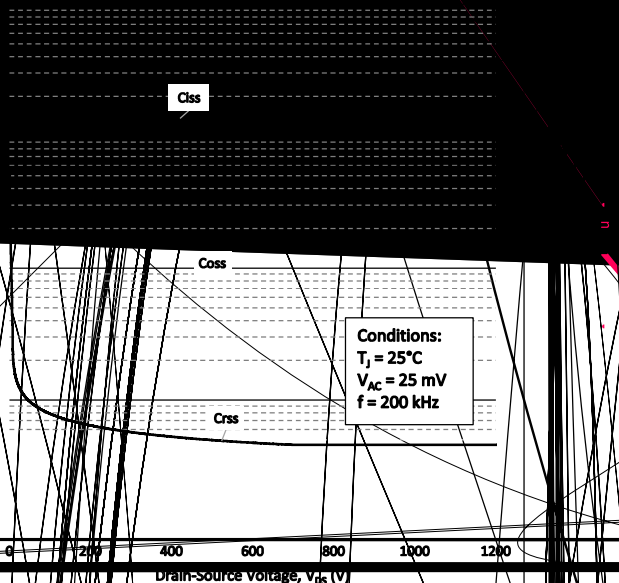


Figure 15. Capacitance vs Drain-Source Voltage

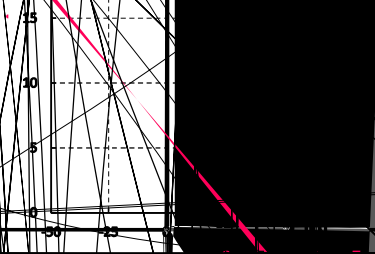
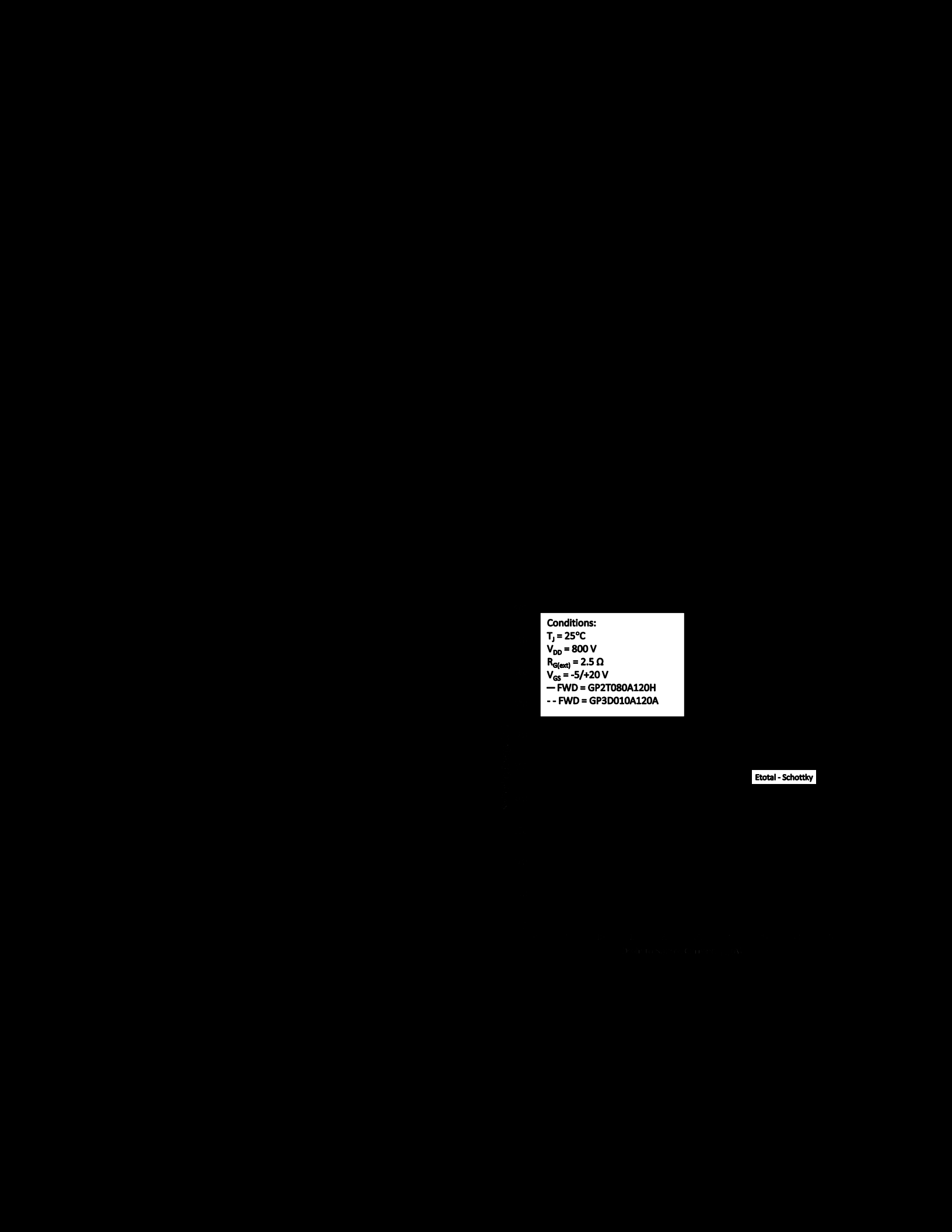


Figure 16. Continuou… g vs. Case Te… ure


Conditions:
T_J = 25°C
V_{DD} = 800 V
$R_{G(ext)}$ = 2.5 Ω
V_{GS} = -5/+20 V
— FWD = GP2T080A120H
- - FWD = GP3D010A120A
Etotal - Schottky

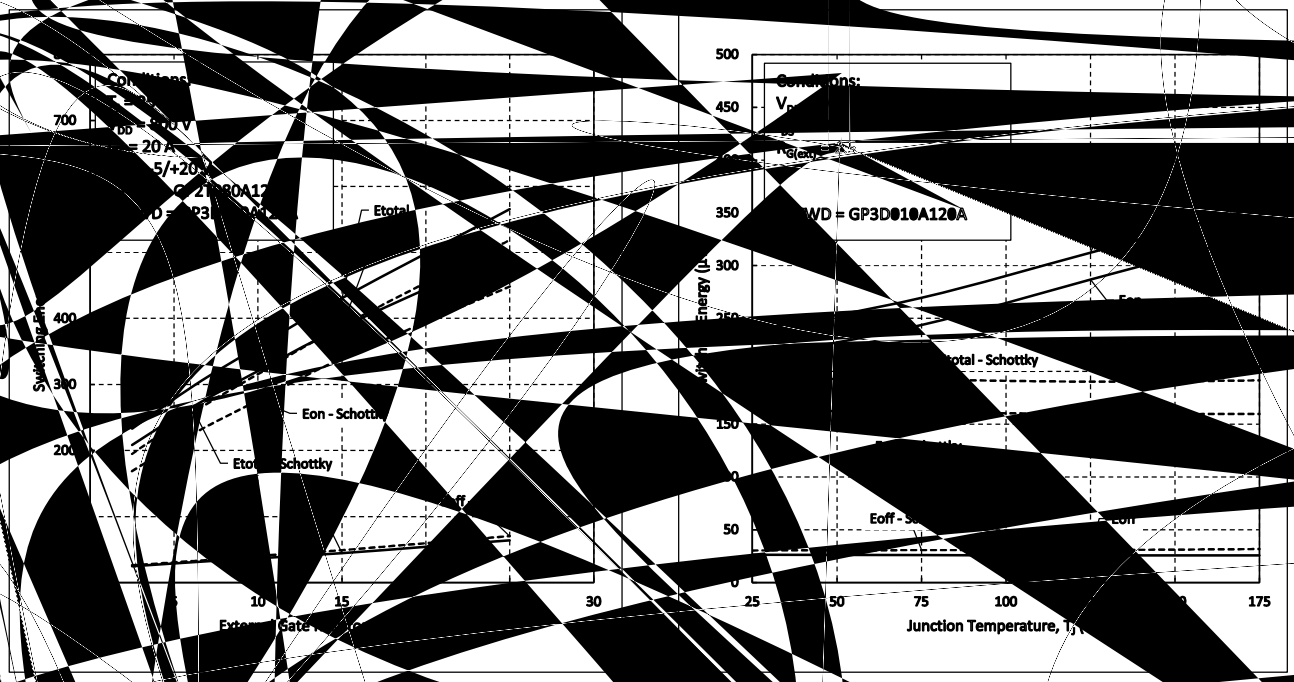


Figure 21. [illegible] Switching Energy [illegible] Figure 22. Clamped [illegible] V vs. Temperature

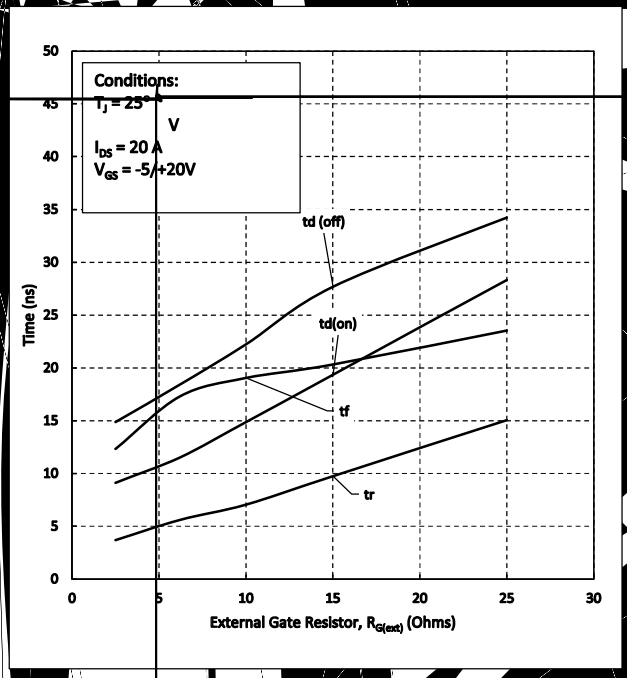


Figure 23. Switching Times vs [illegible]

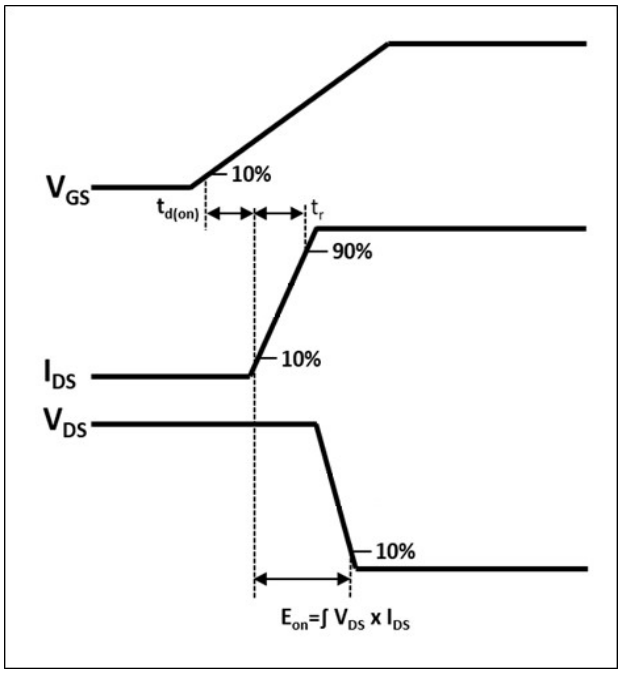


Figure 25. Turn-on Transient Definitions

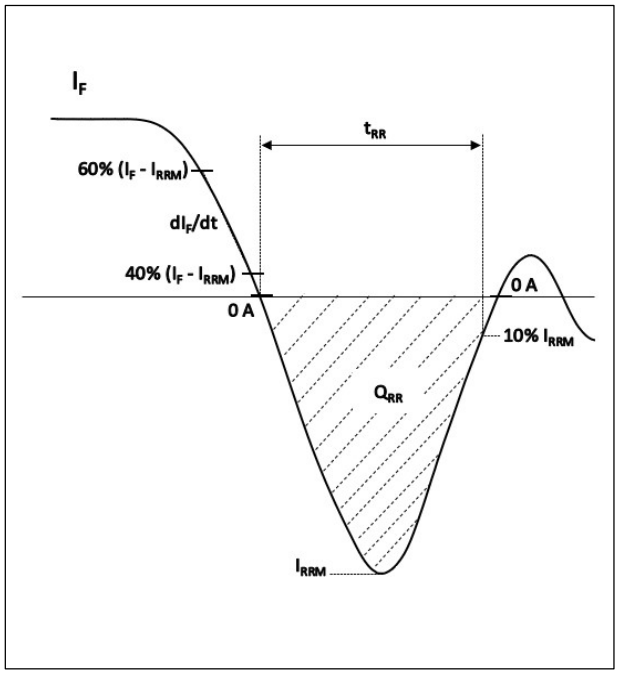
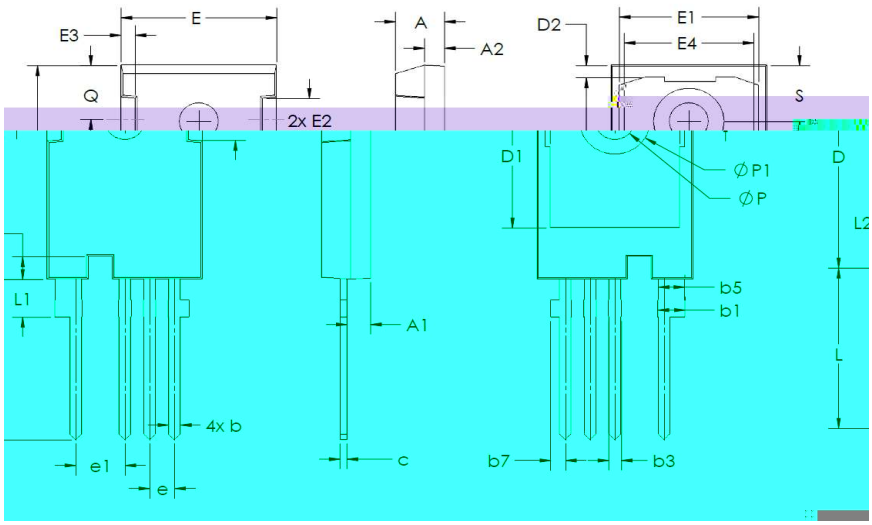


Figure 26. Reverse Recovery Definitions

Package Dimensions TO-247-4L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.07	1.33	0.042	0.052
b1	2.39	2.94	0.094	0.116
b3	1.07	1.60	0.042	0.063
b5	2.39	2.69	0.094	0.106
b7	1.30	1.70	0.051	0.067
c	0.55	0.68	0.022	0.027
c1	0.55	0.65	0.022	0.026
D	23.30	23.60	0.917	0.929
D1	16.25	17.65	0.640	0.695
D2	0.95	1.25	0.037	0.049
E	15.75	16.13	0.620	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	1.90	0.039	0.075
E4	12.38	13.43	0.487	0.529
e	2.54 BSC		0.100 BSC	
e1	5.08 BSC		0.200 BSC	
L	17.31	17.82	0.681	0.702
L1	3.97	4.37	0.156	0.172
L2	2.35	2.65	0.093	0.104
φP	3.51	3.65	0.138	0.144
φP1	7.19 REF		0.283 REF	
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

REACh Compliance

REACh substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future,please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

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